TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7S04F, TC7S04FU

INVERTER

The TC7S04 is a high speed C2MOS INVERTER fabricated with silicon gate C2MOS technology.

It achieves high speed operation similar to equivalent LSTTL while maintaining the C2MOS low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

The input is equipped with protection circuits against static discharge or transient excess voltage.

Output currents are 1/2 compared to TC74HC series models.

FEATURES

•	High Speed	 $t_{pd} = 7ns$	(Typ.)	at
		$V_{CC} = 5V$		

Low Power Dissipation ICC = 1μ A (Max.) at

 $Ta = 25^{\circ}C$

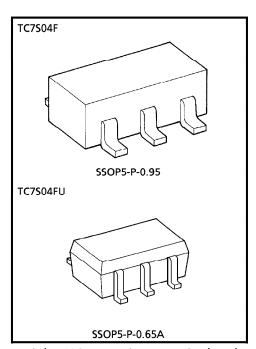
High Noise Immunity $V_{NIH} = V_{NIL}$ = 28% V_{CC} (Min.)

Output Drive Capability 5 LSTTL Loads

Symmetrical Output Impedance ... $|I_{OH}| = I_{OL}$ = 2mA (Min.)

Balanced Propagation Delays $t_{pLH} = t_{pHL}$

Wide Operating Voltage Range ... $V_{CC(opr)} = 2 \sim 6V$

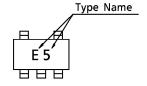


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A: 0.006g (Typ.)

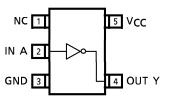
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~7	V
DC Input Voltage	VIN	-0.5~V _{CC} +0.5	V
DC Output Voltage	VOUT	$-0.5 \sim V_{CC} + 0.5$	٧
Input Diode Current	ΙΚ	± 20	mΑ
Output Diode Current	lok	± 20	mΑ
DC Output Current	IOUT	± 12.5	mΑ
DC V _{CC} / Ground Current	lcc	± 25	mΑ
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10s)	TL	260	°C

MARKING



PIN ASSIGNMENT (TOP VIEW)



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CIRCUIT DIAGRAM



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	2~6	V
Input Voltage	VIN	0~V _{CC}	V
Output Voltage	Vout	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C
		$0\sim1000 \ (V_{CC}=2.0V)$	
Input Rise and Fall Time	t _r , t _f	$0 \sim 500 \ (V_{CC} = 4.5V)$	ns
		$0 \sim 400 \ (V_{CC} = 6.0V)$	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION			$Ta = 25^{\circ}C$ $Ta = -40 \sim 85^{\circ}C$					UNIT
CHARACTERISTIC	3 TIVIBOL			Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT
High Loyal				2.0	1.5	_	_	1.5	_	
High-Level Input Voltage	VIH		_	4.5	3.15	_	—	3.15	_	V
input voltage				6.0	4.2	_	_	4.2	_	
Low-Level				2.0	_	—	0.5	—	0.5	
Input Voltage	∨ _{IL}		_	4.5	 	—	1.35	—	1.35	V
input voitage				6.0	_	_	1.8	_	1.8	
	VOH			2.0	1.9	2.0	_	1.9	_	
Iliah Laval			$I_{OH} = -20\mu A$	4.5	4.4	4.5	—	4.4	_	
High-Level		V _{OH} V _{IN} = V _{IL}		6.0	5.9	6.0	_	5.9	_	V
Output Voltage			I _{OH} = -2mA	4.5	4.18	4.31	_	4.13	_	
			$I_{OH} = -2.6mA$	6.0	5.68	5.80	_	5.63	_	
				2.0	_	0.0	0.1	_	0.1	
l avvil aval			$I_{OL} = 20 \mu A$	4.5	<u> </u>	0.0	0.1	_	0.1	
Low-Level	VOL	$V_{IN} = V_{IH}$		6.0	_	0.0	0.1	_	0.1	V
Output Voltage			$I_{OL} = 2mA$	4.5		0.17	0.26	_	0.33	
			$I_{OL} = 2.6 mA$	6.0	_	0.18	0.26	_	0.33	i .
Input Leakage	IN	V _{IN} = V _{CC} (or GND	6.0			± 0.1		± 1.0	
Current										μ A
Quiescent Supply Current	Icc	$V_{IN} = V_{CC}$	or GND	6.0	_	_	1.0	_	10.0	

Output currents are 1/2 compared to TC74HC series models.

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The information contained herein is subject to change without notice.

AC ELECTRICAL CHARACTERISTICS (C _L = 15p	oF, Input $t_r = t_f = 6$ ns, $V_{CC} = 5V$)
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CHARACTERISTIC	SYMBOL	TEST CONDITION	Т	UNIT		
CHARACTERISTIC	STIVIBUL	TEST CONDITION	MIN.	TYP.	MAX.	UNII
Output Transition	tTLH			5	10	ns
Time	tTHL	_		,	10	113
Propagation Delay	t _{pLH}			7	15	nc
Time	t _{pHL}	_		_ ′	13	ns

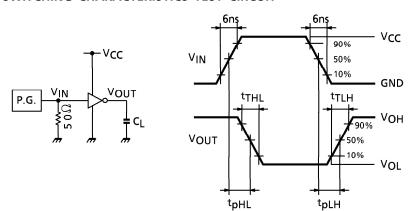
AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

CHARACTERISTIC	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -4	UNIT	
CHARACTERISTIC	STIVIDOL	TEST CONDITION	Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT
Output Transition	t		2.0	_	50	125	_	155	
1	t _{TLH}	_	4.5	<u> </u>	14	25	_	31	ns
Time	t _{THL}		6.0	_	12	21	—	26	
Propagation Dalay	4		2.0	_	48	100	_	125	
Propagation Delay	t _{pLH}	_	4.5	<u> </u>	12	20	—	25	ns
Time	t _{pHL}		6.0	—	9	17	—	21	
Input Capacitance	CIN	_		_	5	10	_	10	
Power Dissipation Capacitance	C _{PD}	(Note 1)		_	10	_	_	_	pF

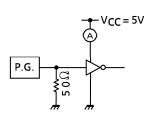
Note 1: CpD defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

Average operating current can be obtained by the equation hereunder.

SWITCHING CHARACTERISTICS TEST CIRCUIT



ICC (opr) TEST CIRCUIT



input waveform is the same as that in case of switching characteristics test.